

PSICS2DP1200V10N

Schoktty Barrier Diode

Feature

- Negligible reverse recovery
- Positive Temperature Coefficient on V_F
- Temperature-Independent Switching
- Fast switching
- > Pb-free / RoHS compliant
- Low switching loss
- Higher frequency
- Low heat dissipation requirements
- Reduce size and cost of the system
- ➢ High-reliability



TO-252-2L



Circuit Diagram

Applications

- Solar inverters
- Uninterruptable power supplies
- Motor drives
- Power Factor Correction

Absolute maximum rating@25°C

Parameter			Value	Units
Repetitive Peak Reverse Voltage			1200	V
Surge Peak Reverse Voltage			1200	V
DC Peak Reverse Voltage	V _R	1200	V	
Continuous Forward Current	T _c =25°C		25	
	T _c =135°C	I _F	13	A
	T _c =148°C		10	
Non-repetitive Forward Surge Current	T _c =25°C,t _p =8.3ms,Half Sine Pulse	I _{FSM}	90	А
Power Dissipation	T _c =25°C	P _{tot}	125	W
Operating Junction and Storage	T _J ,T _{STG}	-55~+175	°C	

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Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Forward Voltage	V _F	I _F = 10A, T _J =25°C	-	1.45	1.8	V
		I _F = 10A, T _J =175°C	-	2.0	-	
Reverse Current	I _R	V _R = 1200V, T _J =25°C	-	6	100	μA
		V _R = 1200V, T _J =175°C	-	30	500	
Total Capacitive Charge	Q _c	V _R = 800V, I _F = 10A di/dt =200A/µs , T _J =25°C	-	25	-	nC
	С	V _R = 0.1V,f = 1MHz	-	600	-	pF
Total Capacitance		V _R = 400V,f = 1MHz	-	45	-	
		V _R = 800V,f = 1MHz	-	34	-	

Thermal Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Units
Thermal Resistance (Junction to case)	R _{θJC}	-	1.2	-	°C/W
Thermal Resistance (Junction to ambient)	R _{θJA}	-	80	-	°C/W
Soldering Temperature	T _{sold}	-	260	-	°C

Typical Characteristics



Fig.1 Forward Characteristics



Fig.2 Reverse Characteristics

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Fig.5 Total Capacitance Charge vs. Reverse Voltage

Fig.6 Transient Thermal Impedance

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Product dimension (TO-252-2L)

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Dim	Millimeters		Inches		
	Min	Мах	Min	Мах	
А	6.30	6.70	0.248	0.264	
В	5.20	5.40	0.205	0.213	
С	1.15	1.35	0.045	0.053	
D	5.70	6.10	0.224	0.24	
E	0.65	0.75	0.026	0.03	
F	2.10	2.50	0.083	0.098	
G	2.20	2.40	0.087	0.095	
н	1.45	1.55	0.057	0.061	
I	2.90	3.10	0.114	0.122	
J	0.45	0.55	0.018	0.022	
К	0.90	1.10	0.035	0.043	

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